Photo Semiconductor Device - Page 1 of 1



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Inclosure Material:
Metal and plastic
Overall Length:
0.114 inches
Overall Diameter:
0.098 inches
Function For Which Designed:
Phototransistor
Internal Configuration:
Junction contact
Mounting Method:
Press fit
Semiconductor Material:
Silicon
Voltage Rating In Volts Per Characteristic:
40.0 collector to emitter voltage/static/base open and 5.0 emitter to collector
Current Rating Per Characteristic:
200.00 milliamperes zero-gate-voltage source current blank
Power Rating Per Characteristic:
100.0 milliwatts small-signal input power, common-collector preset
Maximum Operating Tempurature Per Measurement Point:
150.0 degrees celsius ambient air
Special Features:
Junction pattern arrangement: npn
Terminal Type And Quantity:
1 uninsulated wire lead and 1 case
Shelf Life:
N/a
Unit Of Measure:
Demilitarization:
Yes - demil/mli
Fiig:
A110a0

voltage, dc